

# OPTICAL AND ELECTRO-OPTICAL ENGINEERING SERIES

# ELECTRO-OPTICS HANDBOOK

RONALD WAYNANT MARWOOD EDIGER

# ELECTRO-OPTICS HANDBOOK

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# **ACRONYMS**

2DEG	two dimensional electron gas	CBE	chemical beam epi- taxy
2PA	two photon absorp- tion	CCD	charge coupled de- vice
III-V	Group III, group V of periodic table	CDRH	Center for Devices and Radiological
3HG	third harmonic gen-	CI.	Health (of FDA)
	eration	Ch	choroid
AEL	accessible emission limit	CID	charge-injection de- vice
AM	amplitude modula- tion	CIE	Commission International de l'Eclairage
ANSI	American National Standards Institute	COD	catastrophic optical damage
AO	acousto-optic	CPM	colliding-pulse mode-
APD	avalanche photo-		locked
	diode	cw	continuous wave
APDs	avalanche photo-	$D^*$	detectivity
APM	diodes additive pulse mode	DBR	distributed Bragg re- flector
	locking	DCG	dichromated gelatin
AR	anti reflection	DFB	distributed feedback
ASE	amplified sponta- neous emission	DFDL	distributed feedback dye lasers
BEFWM	Brillouin enhanced four wave mixing	DIN	Deutsche Institüt für
BH	buried heterostruc-	DM	Normung
	ture		depth of modulation
BLIP	background-limited infrared performance	DODCI	diethyloxadicarbon- cyanine iodide
C/S	coupler/splitter	DOES	double heterostruc-
CAD	computer-aided design		ture optoelectronic switches
CAIBE	chemically assisted ion-beam etching	DoF	depth of focus
STATE OF THE STATE		DUT	device under test
CARS	coherent anti-stokes	EA	electron affinity
	Raman spectroscopy	EB	electron beam

xviii ACRONYMS

EBCCD	electron bombarded	GRO	Gamma Ray Observ-
	charge coupled de- vice	COMPE	atory
EBS	electron bombard-	GSMBE	gas source molecular beam epitaxy
ECL	ment silicon emitter-coupled logic	GVD	group velocity dis- persion
EKE	electronic Kerr effect	GVDC	
EL	exposure limits	GVDC	group velocity dis- persion compensa- tion
EMI/ESD	electromagnetic im-	HAZ	heat-affected zone
	pulse/electrostatic discharge	HbO	oxyhemoglobin
EO	electro-optic		(blood)
ESA	excited state absorp-	HBT	heterojunction bipo- lar transistors
FAFAD	fast axial flow with axial discharge	HEAO	High Energy Astronomy Observatory
FDA	Food and Drug Administration	HEMTs	high-electron-mobil- ity transistors
FEL	free electron laser	HID	high intensity dis-
	free electron lasers		charge
FELs FET	field-effect transistors	HOE	holographic optical element
FFT	fast Fourier trans- form	HpD	hematoporphyrin de- rivative
FGC	focusing grating cou-	HR	high reflection
XIII WALL	pler	HR	high resistivity
FHD	flame hydrosis depo- sition	HUD	head-up display
FID	free-induction decay	IC	integrated circuit
FM	frequency modula- tion	ICI	International Commission on Illumina-
FOV	field of view	1D.T	tion
FTFTD	fast transverse flow with transverse dis-	IDT	interdigital trans- ducer
	charge	IEC	International Electrotechnical Commis-
FTP	Fourier transform plane		sion
FWHM	full width half-maxi-	ILD	injection laser diodes
. ,,,,,,,,,	mum	IO	image orthicon
G-R	generation-recombi- nation	IODPU	integrated optic disk pickup
GRIN-SCH	graded index wave- guide separate con-	IOSA	integrated optic spec- trum analyzer
	finement heterostruc- ture	IPC	imaging proportional counter

ACRONYMS xix

ir	infrared	MO	magneto-optic
JFETs	junction FETs	MOCVD	metal organic chemi-
KTP	KTiOPO <sub>4</sub> , potassium tellurium phosphate	MOPA	cal vapor deposition master oscillator
LANs	local area networks	MOTA	power amplifier
LAVA	laser assisted vascu- lar anastomosis	MOS	metal-oxide-semicon- ductor
LDV	laser Doppler velo- cimeter	MOVPE	metal organic vapor phase epitaxy
LED	light emitting diode	MPE	maximum permissi-
lidar	light detection and ranging	MPI	ble exposure multiphoton ioniza- tion
LIF	laser induced fluores- cence	MQW	multiple quantum well
LIS	laser isotope separa- tion	MSM	metal semiconductor
LiTaO <sub>3</sub>	lithium tantalate	MTBF	mean time between
LLLTV	low light level televi- sion	E CALCOLIN	failure
LLNL	Lawrence Livermore	MTF	modulation transfer function
LM	National Laboratory light microscopy	NA	numerical aperture
LPE	liquid phase epitaxy	NALM	nonlinear amplifying loop mirror
LSI	large scale integra- tion	NEP	noise-equivalent power
LSO	laser safety officer	NHZ	nominal hazard zone
LTE	local thermal equilib- rium	NIST	National Institute of Standards and Tech-
LURE	Laboratoire pour I'Utilisation du Ray-	nm	nology nanometers = $10^{-9}$
	onment Electromag- netic	NO	meters
μm	micrometers (mi-	NO	nitric oxide non-linear optic
	crons) = $10^{-6}$ meters	NOHA	nominal ocular haz-
MAMA	multianode micro-		ard area
MBE	channel array molecular beam epi-	NRL	Naval Research Lab- oratory
MCP	taxy	OD	optical density
MES	microchannel plate metal semiconductor	OEIC	optoelectronic inte- grated circuits
ml	mode-locked	OIC	optical integrated cir-
MMIC	monolithic micro- wave integrated cir- cuit	OKE	cuit orientational Kerr ef- fect

**XX** ACRONYMS

OODR	optical-optical double	RIBE	reactive-ion-beam etching
OPD	optical path differ-	RIE	reactive ion etching
OLD	ence	RIKES CARS	Raman-Induced
OPO	optical parametric oscillator		Kerr-effect spectros- copy
OSSE	Oriented Scintillation Spectrometer Experi-	RIMS	resonance ionization mass spectroscopy
	ment	RPM	resonant passive
PAC	photoactive com- pounds	SAFAD	mode-locking slow axial flow with
PC	photoconductive	2 1722	axial discharge
PDT	photodynamic therapy	SAW	surface acoustic waves
PE PES	pigment epithelium	SBN	strontium barium ni- trate
	photoelectron spec- troscopy	SBS	stimulated Brillouin scattering
PFL	pulse forming line	SEBIR	secondary electron
PGC	phase-generated car- rier		bombardment-in- duced response
PLL	phase-locked-loop	SEC	secondary electron
PM	polarization main-		conduction
PMMA	taining polymethyl methac-	SEED	self-electro-optic ef- fect devices
IMMA	rylade	SELFOC	self-focusing
PMT	photomultiplier tube	SEVA	slowly varying enve-
PPCM	passive phase conju-	22,11	lope approximation
	gate mirror	SHG	second harmonic
PVF	polyvinyl fluoride	~~	generation
PWS	port wine stains	SI	semi-insulating
PZT	lead zirconate	SIT	silicon intensified tube
PZT	piezoelectric trans- ducer	SLB	super lattice buffer
QE	quantum-effect	SLD	superluminescent
	-	OLD	diodes
QW	quantum-well	SLM	single longitudinal
RC	resistance-capaci- tance		mode
RE	rare earth	SMF	spectral matching factor
REC	rare earth cobalt	$SNR_D$	signal to noise ratio
REMPT	resonantly enhanced		of a display
	multiphoton ioniza- tion	$SNR_{DT}$	signal to noise ratio
RGH	rare gas halide		of a display at threshold

ACRONYMS XXI

signal to noise ratio	TO	thermo-optic
noise)	TPF	two-photon fluores- cence
self-phase modula- tion	TVL	threshold limit values
single-quantum-well	TVL/PH	television lines/pic- ture height
stimulated Raman scattering	uv	ultraviolet
tetra chlorodibenzo- <i>p</i> dioxin	VCO	voltage-controlled oscillator
trichloroethane	VCSEL	vertical cavity surface
	111.01	emitting lasers
trienthylamine	VLSI	very large scale inte- gration
transmission electron microscopy	VLSIs	very large scale integrated circuits
twin-grating focusing beam splitter	VSTEP	vertical to surface transmission electro-
triglycerine sulfide		photonic
triglycerine selanate	vuv	vacuum ultraviolet
eration	WDM	wavelength division multiplexing
total internal reflec- tion	XPM	cross phase modula-
tetraKis- (dimethylamino) eth- ylene	YAG	yttrium aluminum garnet
trimethylaluminum hydride	YLF	LiYF <sub>4</sub> , lithium yit- trium fluoride
	of video (for white noise) self-phase modulation single-quantum-well stimulated Raman scattering tetra chlorodibenzo-p dioxin trichloroethane transversely excited atmospheric trienthylamine transmission electron microscopy twin-grating focusing beam splitter triglycerine sulfide triglycerine selanate third harmonic generation total internal reflection tetraKis-(dimethylamino) ethylene trimethylaluminum	of video (for white noise)  self-phase modulation  single-quantum-well  stimulated Raman scattering  tetra chlorodibenzo-p dioxin  trichloroethane  transversely excited atmospheric  trienthylamine  transmission electron microscopy  twin-grating focusing beam splitter  triglycerine selanate third harmonic generation  total internal reflection total internal reflection tetraKis- (dimethylamino) ethylene trimethylaluminum  TVL  TVL/PH  TVL/PH  Stimulated Raman  TVL  VCO  VCO  VSEL  VLSI  VLSI  VSTEP  VSTEP  VSTEP  VSTEP  VAG  VYAG

# **CONTENTS IN BRIEF**

Chapter 1. Introduction to Electro-Optics Chapter 2. Noncoherent Sources

Chapter 3.	Ultraviolet, Vacuum-Ultraviolet, and X-Ray
	Lasers
Chapter 4.	Visible Lasers
Chapter 5.	Lasers, Solid-State
Chapter 6.	Semiconductor Lasers
Chapter 7.	Infrared Gas Lasers
Chapter 8.	Free Electron Lasers
Chapter 9.	Ultrashort Laser Pulses
Chapter 10.	Optical Materials—UV, VUV
Chapter 11.	Optical Materials: Visible and Infrared
Chapter 12.	Optical Fibers
Chapter 13.	Nonlinear Optics
Chapter 14.	Phase Conjugation
Chapter 15.	Ultraviolet and X-Ray Detectors
Chapter 16.	Visible Detectors
Chapter 17.	Infrared Detectors
Chapter 18.	Imaging Detectors
Chapter 19.	Holography
Chapter 20.	Laser Spectroscopy and Photochemistry
Chapter 21.	Fiber-Optic Sensors
Chapter 22.	High-Resolution Lithography for
	Optoelectronics
Chapter 23.	Laser Safety in the Research and Development
•	Environment
Chapter 24.	Lasers and Medicine
Chapter 25.	Material Processing Applications of Lasers
Chapter 26.	Optical Integrated Circuits
Chapter 27.	Optoelectronic Integrated Circuits
	a production and discount and d

## **CONTENTS**

Chapter 1. Introduction to Electro-Optics Ronald W. Waynant and

1.1

Contributors

Marwood N. Ediger

Acronyms xvii

Preface

xiii

viii CONTENTS

Chapter 5. Lasers, Solid-State Georg F. Albrecht and Stephen A. Payne	5.1
<ul> <li>5.1. Introduction / 5.1</li> <li>5.2. Solid-State Laser Devices / 5.2</li> <li>5.3. Solid-State Laser Materials / 5.28</li> <li>5.4. Future Directions / 5.48</li> <li>5.5. References / 5.49</li> </ul>	
Chapter 6. Semiconductor Lasers James J. Coleman	6.1
<ul> <li>6.1. Compound Semiconductors and Alloys / 6.1</li> <li>6.2. Energy Band Structure / 6.3</li> <li>6.3. Heterostructures / 6.6</li> <li>6.4. Double Heterostructure Laser / 6.7</li> <li>6.5. Stripe Geometry Lasers / 6.11</li> <li>6.6. Index-Guided Stripe Geometry Lasers / 6.12</li> <li>6.7. Materials Growth / 6.14</li> <li>6.8. Quantum Well Heterostructure Lasers / 6.15</li> <li>6.9. Laser Arrays / 6.18</li> <li>6.10. Modulation of Laser Diodes / 6.21</li> <li>6.11. Reliability / 6.23</li> <li>6.12. References / 6.25</li> </ul>	
Chapter 7. Infrared Gas Lasers Michael Ivanco and Paul A. Rochefort	7.1
<ul> <li>7.1. Introduction / 7.1</li> <li>7.2. Gas Laser Theory / 7.2</li> <li>7.3. Specific Gas Lasers / 7.13</li> <li>7.4. Conclusions / 7.33</li> <li>7.5. References / 7.33</li> </ul>	
Chapter 8. Free-Electron Lasers John A. Pasour	8.1
8.1. Introduction / 8.1 8.2. FEL Theory / 8.3 8.3. FEL Components / 8.9 8.4. FEL Devices / 8.16 8.5. Future Directions / 8.18 8.6. Conclusions / 8.20 8.7. References / 8.21	
Chapter 9. Ultrashort Laser Pulses Li Yan, P. T. Ho, and Chi H. Lee	9.1
<ul> <li>9.1. Theory of Ultrashort Pulse Generation / 9.1</li> <li>9.2. Methods of Generation / 9.5</li> <li>9.3. Ultrashort Pulse Laser Systems / 9.17</li> <li>9.4. Methods of Pulsewidth Measurements / 9.26</li> <li>9.5. Application of Ultrafast Optics to High-Frequency Electronics / 9.31</li> <li>9.6. Conclusions / 9.38</li> <li>9.7. References / 9.39</li> </ul>	

Chapter 10. Optical Materials—UV, VUV Jack C. Rife	10.1
10.1. Fundamental Physical Properties / 10.3 10.2. Transmissive UV Optics / 10.7 10.3. Reflective UV Optics / 10.16 10.4. Damage and Durability / 10.26 10.5. Fabrication / 10.31 10.6. References / 10.37	
Chapter 11. Optical Materials: Visible and Infrared W. J. Tropf, T. J and M. E. Thomas	. <i>Harris,</i> 11.1
11.1. Introduction / 11.1 11.2. Types of Materials / 11.1 11.3. Applications / 11.3 11.4. Material Properties / 11.5 11.5. Property Data Tables / 11.10 11.6. References / 11.84	
Chapter 12. Optical Fibers Carlton M. Truesdale	12.1
12.1. Theory of Fiber Transmission / 12.1 12.2. Materials for the Fabrication of Optical Fiber / 12.10 12.3. Fabrication Methods / 12.12 12.4. Fiber Losses / 12.16 12.5. Pulse Broadening / 12.19 12.6. References / 12.27	
Chapter 13. Nonlinear Optics Gary L. Wood and Edward J. Sharp	13.1
13.1. Introduction / $13.1$ 13.2. Linear Optics: The Harmonic Potential Well / $13.2$ 13.3. Nonlinear Optics: The Anharmonic Potential Well / $13.4$ 13.4. Second-Order Nonlinearities: $\chi^{(2)}$ / $13.8$ 13.5. The Third-Order Susceptibilities: $\chi^{(3)}$ / $13.10$ 13.6. Propagation through Nonlinear Materials / $13.14$ 13.7. Acknowledgments / $13.30$ 13.8. References / $13.31$	
Chapter 14. Phase Conjugation Gary L. Wood	14.1
14.1. Phase Conjugation: What it is / 14.1 14.2. Phase Conjugation: How to Generate it / 14.4 14.3. Applications / 14.33 14.4. References / 14.37	
Chapter 15. Ultraviolet and X-Ray Detectors George R. Carruthers	15.1
15.1. Overview of Ultraviolet and X-Ray Detection Principles / 15.1 15.2. Photographic Film / 15.1	

X CONTENTS

15.4. 15.5. 15.6. 15.7.	Nonimaging Photoionization Detectors / 15.2 Imaging Proportional Counters / 15.7 Photoemissive Detectors / 15.10 Solid-State Detectors / 15.28 Scintillation Detectors / 15.35 References / 15.36	
Chap	ter 16. Visible Detectors Suzanne C. Stotlar	16.1
16.2. 16.3. 16.4. 16.5. 16.6.	Introduction / 16.1 The Human Eye as a Detector / 16.4 Photographic Film / 16.6 Photoelectric Detectors / 16.7 Thermal Detectors / 16.16 Other Detectors / 16.21 Detection Systems and Selection Guide / 16.21 References and Further Reading / 16.23	
Chap	ter 17. Infrared Detectors Suzanne C. Stotlar	17.1
17.2. 17.3. 17.4. 17.5. 17.6.	Introduction / 17.1 Photographic Film / 17.1 Photoelectric Detectors / 17.2 Thermal Detectors / 17.14 Other Detectors / 17.22 Detection Systems and Selection Guide / 17.23 References and Further Reading / 17.24	
Chap	ter 18. Imaging Detectors Frederick A. Rosell	18.1
18.2. 18.3. 18.4. 18.5. 18.6. 18.7.	Introduction / 18.1 Photosurfaces / 18.2 Imaging Tubes / 18.5 Solid-State Imaging Devices / 18.11 Imaging System Performance Model / 18.14 Modulation Transfer Functions / 18.20 Applications / 18.24 References / 18.24	
Chap	ter 19. Holography <i>Tung H. Jeong</i>	19.1
19.2. 19.3. 19.4. 19.5. 19.6.	Introduction / 19.1 Theory of Holographic Imaging / 19.1 Volume Holograms—A Graphic Model / 19.6 Material Requirements / 19.9 General Procedures / 19.12 Current Applications / 19.13 References / 19.15	

Chapter 20. Laser Spectroscopy and Photochemistry G. Rodriguez, S. B. Kim, and J. G. Eden	20.1
<ul> <li>20.1. Introduction / 20.1</li> <li>20.2. Laser-Induced Fluorescence and Absorption Spectroscopy / 20.3</li> <li>20.3. Photoionization and Photoelectron Spectroscopy / 20.16</li> <li>20.4. Multiphoton Spectroscopy / 20.22</li> <li>20.5. Nonlinear Laser Spectroscopy / 20.26</li> <li>20.6. Photochemistry / 20.42</li> <li>20.7. Concluding Comments / 20.48</li> <li>20.8. Acknowledgments / 20.48</li> <li>20.9. References / 20.49</li> </ul>	
Chapter 21. Fiber-Optic Sensors Charles M. Davis and Clarence J. Zarobila	21.1
21.1. Introduction / 21.1 21.2. Fiber-Optic Sensor Transduction / 21.1 21.3. Fiber-Optic Sensor Components / 21.10 21.4. Temperature Sensors / 21.14 21.5. Static and Dynamic Pressure Sensors / 21.16 21.6. Accelerometers / 21.20 21.7. Rate-of-Rotation Sensors / 21.23 21.8. Magnetic/Electric Field Sensors / 21.24 21.9. References / 21.27	
Chapter 22. High-Resolution Lithography for Optoelectronics Martin Peckerar, P. T. Ho, and Y. J. Chen	22.1
<ul> <li>22.1. Introduction / 22.1</li> <li>22.2. Fundamentals of Lithography / 22.2</li> <li>22.3. Lithographic Techniques Useful in Optoelectronic Device Fabrication / 22.6</li> <li>22.4. Examples / 22.23</li> <li>22.5. Concluding Remarks / 22.36</li> <li>22.6. Acknowledgments / 22.37</li> <li>22.7. References / 22.37</li> </ul>	
Chapter 23. Laser Safety in the Research and Development Environment David H. Sliney	23.1
23.1. Introduction / 23.1 23.2. Biological Effects / 23.2 23.3. Safety Standards / 23.4 23.4. Risk of Exposure / 23.5 23.5. Laser Hazard Classification / 23.8 23.6. Laser Hazard Assessment / 23.13 23.7. Laser System Safety / 23.14 23.8. The Safe Industrial Laser Laboratory / 23.15 23.9. Laser Eye Protection / 23.18 23.10. Laser Accidents / 23.26 23.11. Electrical Hazards / 23.26 23.12. Visitors and Observers / 23.26 23.13. Delayed Effects and Future Considerations / 23.27	

xii CONTENTS

23.14. Conclusions and General Guidelines / 23.27 23.15. References / 23.28

Index follows Chapter 27 I.1

Chapter 24. L	asers in Medicine	Ashley J. Welch and M.	. J. C. van Gemert	24.1
24.3. Medical A 24.4. Ablation 24.5. Photocher 24.6. Photoacou	nermal Interactions / 24.18 pplications / 24.18 / 24.29 nical Interactions / 24.3 rections / 24.34	32		
Chapter 25. N James T. Luxon	laterial Processing	Applications of Laser	rs	25.1
25.2. Laser Cha Disadva 25.3. Laser Sur 25.4. Welding a 25.5. Cutting ar 25.6. Marking	ntages / 25.5 face Modification / 25.7 25.9 ad Drilling / 25.12 / 25.13 tronics Applications / 2	Processing: Advantages	and	
Chapter 26. O and Toshiaki Su		cuits <i>Hiroshi Nishiha</i>	ara, Masamitsu Har	una, 26.1
26.2. Waveguide 26.3. Grating C 26.4. Passive W 26.5. Functiona	aveguide Devices / 26. Waveguide Devices / of Optical Integrated C	Tabrication / 26.1 ntegrated Circuits / 26.18 26.26	10	
Chapter 27. O	ptoelectronic Integr	ated Circuits Osamo	u Wada	27.1
<ul><li>27.3. Materials,</li><li>27.4. Optoelectron</li></ul>	and Features / 27.1 Basic Devices, and Fabronic Integrated Circuits oplications / 27.20 / 27.23	rication Techniques / 2 / 27.11	7.3	

### CHAPTER 1

# INTRODUCTION TO ELECTRO-OPTICS

Ronald W. Waynant and Marwood N. Ediger

#### 1.1 INTRODUCTION

The field of electro-optics has become increasingly more important in the last 20 years as its prodigies and applications have found their way into most facets of science, industry, and domestic use. This near-revolution, which essentially started with the advent of the laser, has been the result of extensive parallel and often symbiotic development of sources, materials, and microelectronics. The combination of these technologies has enabled a great variety of compact devices with ever greater intelligence and performance. If source development was instrumental in initiating the field, materials and detectors were the binding elements. Vast improvements in optical materials have made fiber optics feasible and the availability of high-quality, affordable fibers has, in turn, made optical circuits and a variety of optical sensors possible. Refinement and development of new materials have resulted in an astonishing variety of devices to modulate, polarize, frequency-shift, and otherwise control coherent radiation. In turn, detectors have achieved greater performance and smaller size and cost.

This handbook attempts to cover a broad spectral bandwidth—from x-rays to far infrared. A primary motivation in extending the short-wavelength limit of the source spectrum, and the handbook's coverage of it, is the demand for higher resolving powers in materials and device fabrication applications as well as medical and biological imaging. Figure 1.1 depicts the size of objects of interest in the biological, materials science, and electronics worlds, and the wavelength necessary to resolve them as prescribed by the Rayleigh criterion. The infrared boundaries of the spectrum are also continually being strained by sources, materials, and detectors in the development of a variety of applications such as imaging, optical diagnostics, and spectroscopy.

Each chapter of this handbook falls into one of four categories: sources, materials, and their properties (e.g., nonlinear optics), detectors, and applications. In the remainder of this chapter we present some simple overlying principles of each category and a topical map to aid the reader in finding the desired information.

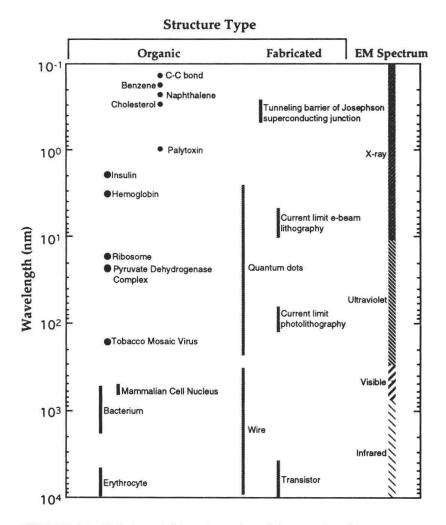


FIGURE 1.1 Relation of object size and resolving wavelength.

#### 1.2 TYPES OF LIGHT SOURCES

Chapter 2 takes a detailed look at incoherent sources, and Chaps. 3 through 8 are devoted to the numerous laser sources grouped in part by media and in part by wavelength. Ultrashort pulse lasers and techniques are covered in Chap. 9.

Although the activity in the field of electro-optics has often been mirrored by events in laser development, incoherent sources still have an important role. Lasers are much newer and more space is devoted to them in the chapters to follow; however, the inescapable fact is that lamps currently have a much greater effect on our everyday lives than do lasers. With hundreds of millions of plasma discharge lamps and billions of incandescent light bulbs in constant use on a worldwide basis, power expenditure on lighting alone approaches the Terawatt level. Even the 22 percent or lower efficiency of most lamps still exceeds that of most lasers.

Arc lamps are characterized by high currents (several amperes) and high pressures (atmospheres) with ballast resistors used to prevent complete runaway. The lamps can be exceedingly bright. Examples include high-pressure (3 to 10 atmo-